

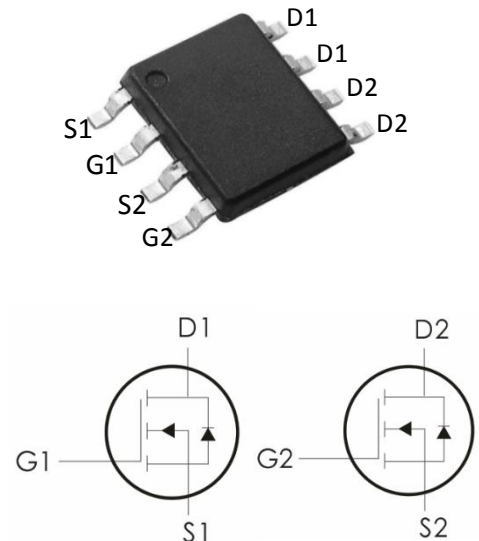
Description:

This Dual N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=20V, I_D=10A, R_{DS(on)} < 21m\Omega @ V_{GS}=4.5V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 10	V
I_D	Continuous Drain Current - $T_A=25^\circ C$	10	A
	Continuous Drain Current - $T_A=100^\circ C$	6	
I_{DM}	Drain Current-Pulsed	40	A
P_D	Power Dissipation - $T_A=25^\circ C$	2	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$

Package Marking and Ordering Information:

Part NO.	Marking	Package
DOS10DN02	10DN02	SOP-8D

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =20V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 12V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	0.5	0.7	1	V
R _{DS(ON)}	Drain-Source On Resistance②	V _{GS} =4.5V, I _D =4A	---	16	21	m Ω
		V _{GS} =2.5V, I _D =3A	---	20	30	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	775	---	pF
C _{Oss}	Output Capacitance		---	135	---	
C _{rss}	Reverse Transfer Capacitance		---	75	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =10V, I _D =3.5A R _G =3 Ω . V _{GS} =4.5V,	---	8.5	---	ns
t _r	Rise Time		---	29	---	ns
t _{d(off)}	Turn-Off Delay Time		---	34	---	ns
t _f	Fall Time		---	9.5	---	ns
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =3.5A	---	10	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	2.8	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Forward Voltage②	V _{GS} =0V, I _{SD} =6.8A	---	---	1.2	V
I _S	Source drain current(Body Diode)	T _A =25℃	---	---	6.8	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_C=25^\circ C$ unless otherwise noted)

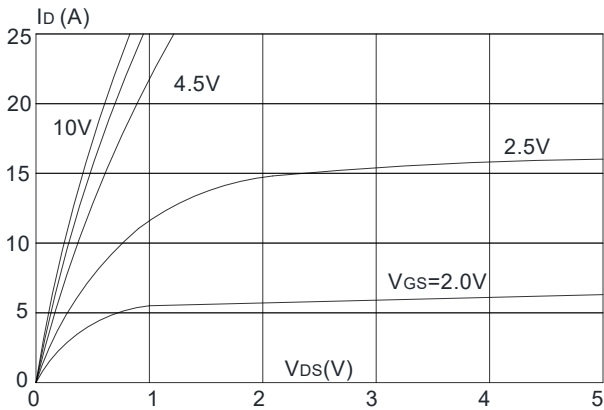


Figure 1: Output Characteristics

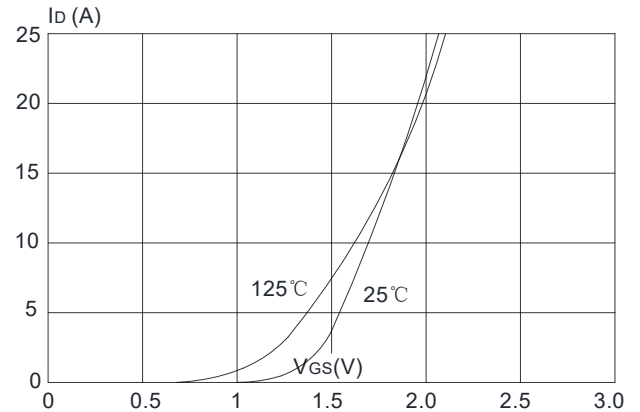


Figure 2: Typical Transfer Characteristics

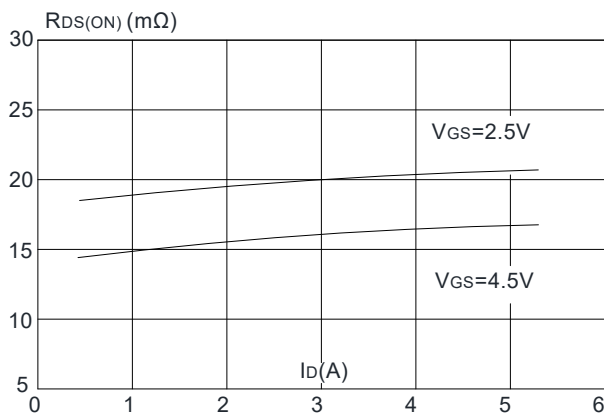


Figure 3: On-resistance vs. Drain Current

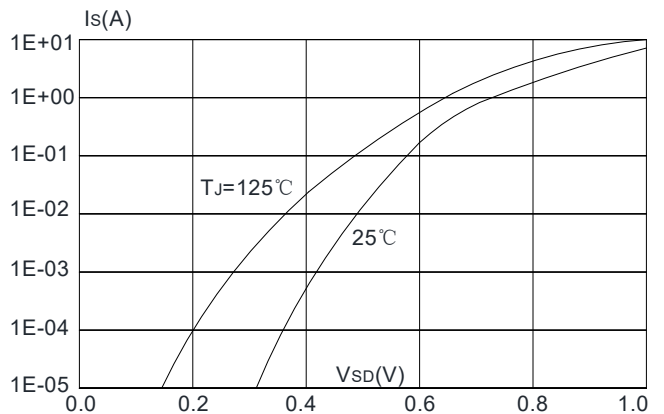


Figure 4: Body Diode Characteristics

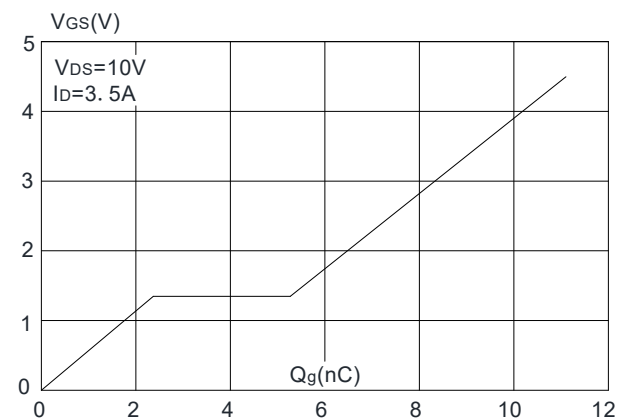


Figure 5: Gate Charge Characteristics

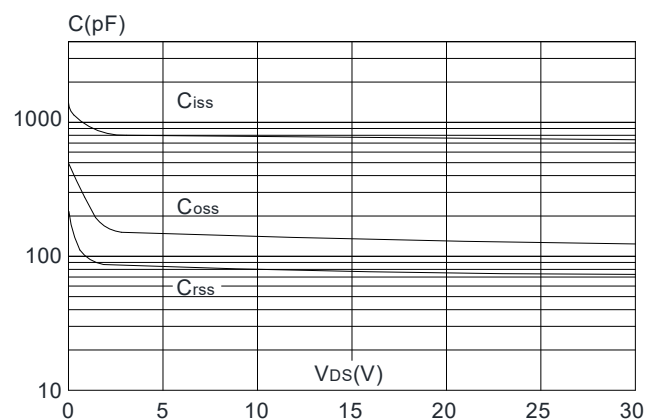


Figure 6: Capacitance Characteristics

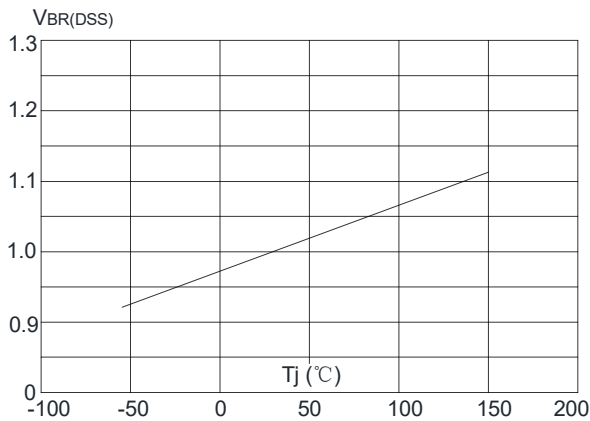


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

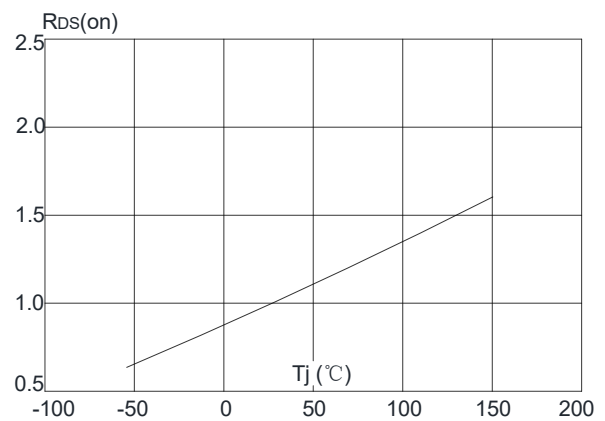


Figure 8: Normalized on Resistance vs. Junction Temperature

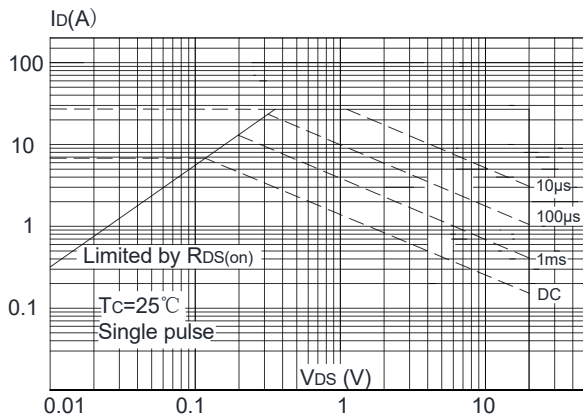


Figure 9: Maximum Safe Operating Area

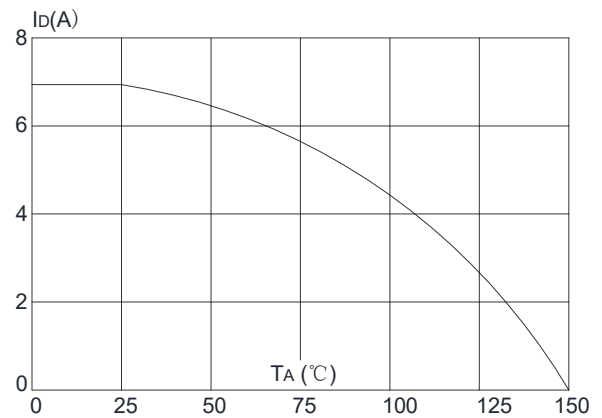


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

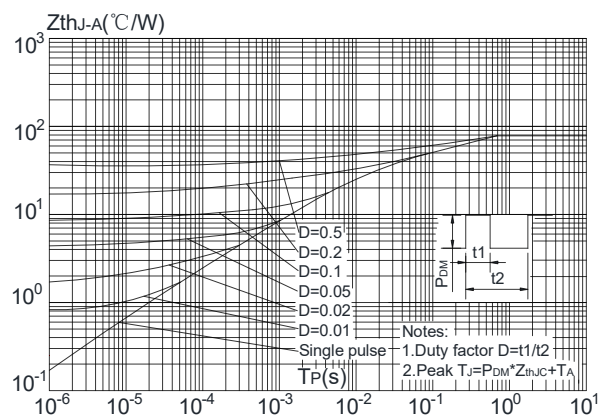


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient